| | | | HK. |
|--|---|---|--------------------------|
| | Application No. | Applicant(s) | |
| Madina of Allaceshiller | 10/709,469 | HUANG ET AL. | |
| Notice of Allowability | Examiner | Art Unit | |
| | David Nhu | 2818 | |
| The MAILING DATE of this communication appeal. All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RID of the Office or upon petition by the applicant. See 37 CFR 1.313 | (OR REMAINS) CLOSED in this apport or other appropriate communication GHTS. This application is subject to | plication. If not included will be mailed in due c | d ourse. T HIS |
| 1. X This communication is responsive to 6/7/05. | | | |
| 2. X The allowed claim(s) is/are <u>1-23</u> . | | | |
| 3. ☑ The drawings filed on <u>07 June 2005</u> are accepted by the E | xaminer. | | |
| 4. Acknowledgment is made of a claim for foreign priority una) All b) Some* c) None of the: 1. Certified copies of the priority documents have 2. Certified copies of the priority documents have 3. Copies of the certified copies of the priority documents have International Bureau (PCT Rule 17.2(a)). * Certified copies not received: Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDONM THIS THREE-MONTH PERIOD IS NOT EXTENDABLE. 5. A SUBSTITUTE OATH OR DECLARATION must be subm INFORMAL PATENT APPLICATION (PTO-152) which give 6. CORRECTED DRAWINGS (as "replacement sheets") mus (a) including changes required by the Notice of Draftspers 1) hereto or 2) to Paper No./Mail Date (b) including changes required by the attached Examiner's Paper No./Mail Date Identifying indicia such as the application number (see 37 CFR 1 each sheet. Replacement sheet(s) should be labeled as such in to the deponant of the dep | e been received. been received in Application No cuments have been received in this of this communication to file a reply IENT of this application. itted. Note the attached EXAMINER es reason(s) why the oath or declarate of the submitted. son's Patent Drawing Review (PTO- s Amendment / Comment or in the Comment or in the Comment of the drawing he header according to 37 CFR 1.121(sit of BIOLOGICAL MATERIAL I | national stage application complying with the requestion is deficient. SAMENDMENT or Notation is deficient. Settion of the front (not the line). The submitted of the submitted of the submitted of the submitted. | DTICE OF |
| | | , LE IVIV (TEIXIV LE. | |
| Attachment(s) 1. ⊠ Notice of References Cited (PTO-892) | 5. Notice of Informal F | Patent Application (PTC |)-152) |
| 2. Notice of Draftperson's Patent Drawing Review (PTO-948) | 6. Interview Summary | • | |
| 3. Information Disclosure Statements (PTO-1449 or PTO/SB/0 | | ment/Comment | |
| 4. Examiner's Comment Regarding Requirement for Deposit of Riological Material | 8. ⊠ Examiner's Statement9. □ Other | ent of Reasons for Allov | wance |
| of Biological Material | | 82 | |

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REASONS FOR ALLOWANCE

1. Claims 1-23 are allowed.

- The following is an examiner's statement of reasons for allowance: None of the references of record teaches or suggests as cited in claims 1, 15: forming a first gate and a second gate beside respective sidewalls of the trench wherein the first gate and the second gate are at a distance from each other and expose a portion of the first dielectric layer at a bottom of the trench; removing a portion of the passivation layer, the second dielectric layer and the first dielectric layer to expose a substrate surface at the bottom of the trench; performing a etching back process so that a top section of the conductive layer is at a level higher than an upper surface of the liner layer but lower than an upper surface of the mask layer; forming a pair of spacers on respective sidewalls of the trench so that a portion of the conductive layer is covered; removing a portion of the conductive layer using the spacers and the mask layer as an etching mask to form a first floating agte on the respective sidewalls of the trench; removing portions of the passivation layer, the first inter-gate dielectric layer and the tunneling oxide layer until a portion of the substrate at the bottom of the trench is exposed; forming a control gate that completely fills the trench, wherein a top section of the trench control gate is at a level higher than a top section of both the first floating gate and the second floating gate.
- 3. Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

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Conclusion

4. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure: Mei et al (6,130,453): Flash Memory Structure with Floating Gate in Vertical Trench.

5. Any inquiry concerning this communication on earlier communications from the examiner should be directed to David Nhu, (571)272-1792. The examiner can normally be reached on Monday-Friday from 7:30 AM to 5:00 PM.

The examiner's supervisor, David Nelms can be reached on (571)272-1787.

The fax phone number for the organization where this application or proceeding is assigned is (703)872-9306.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956

David Nhu

June 17, 2005

PRIMARY EXAMMER

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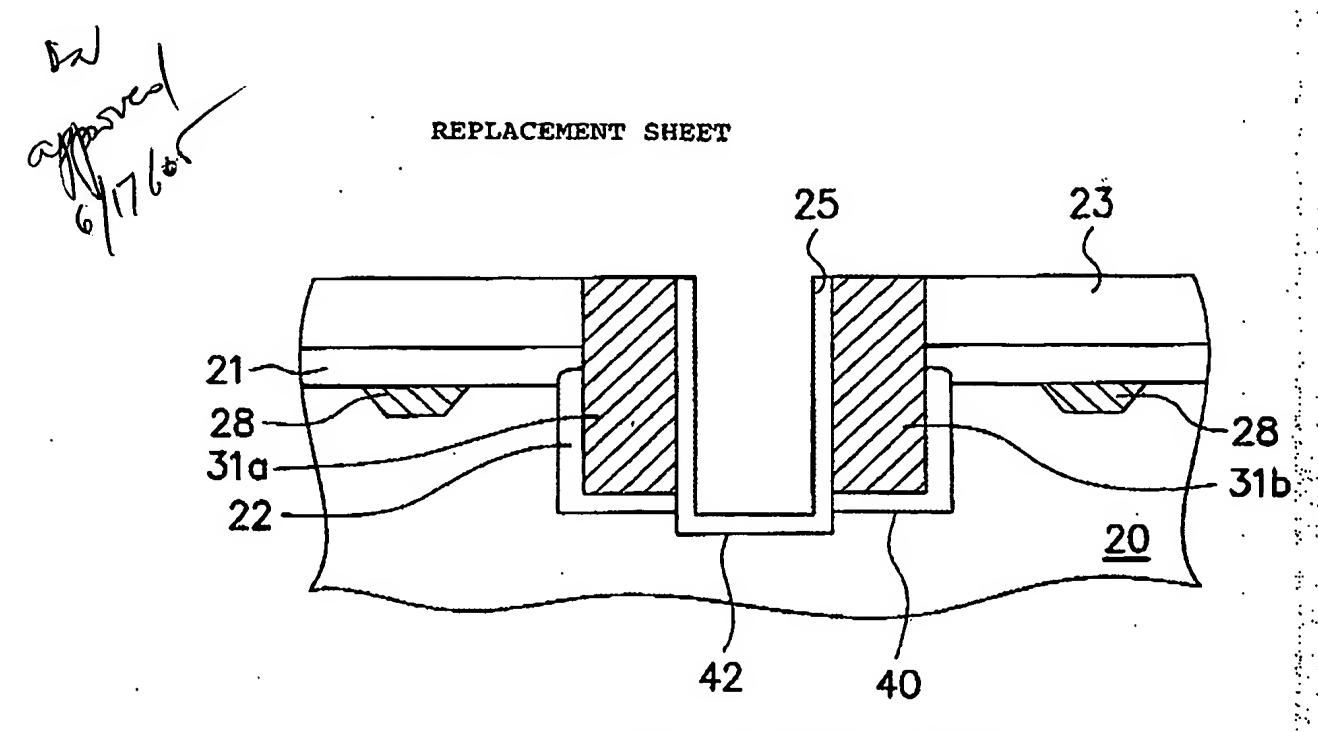


FIG. 2C(PRIOR ART)

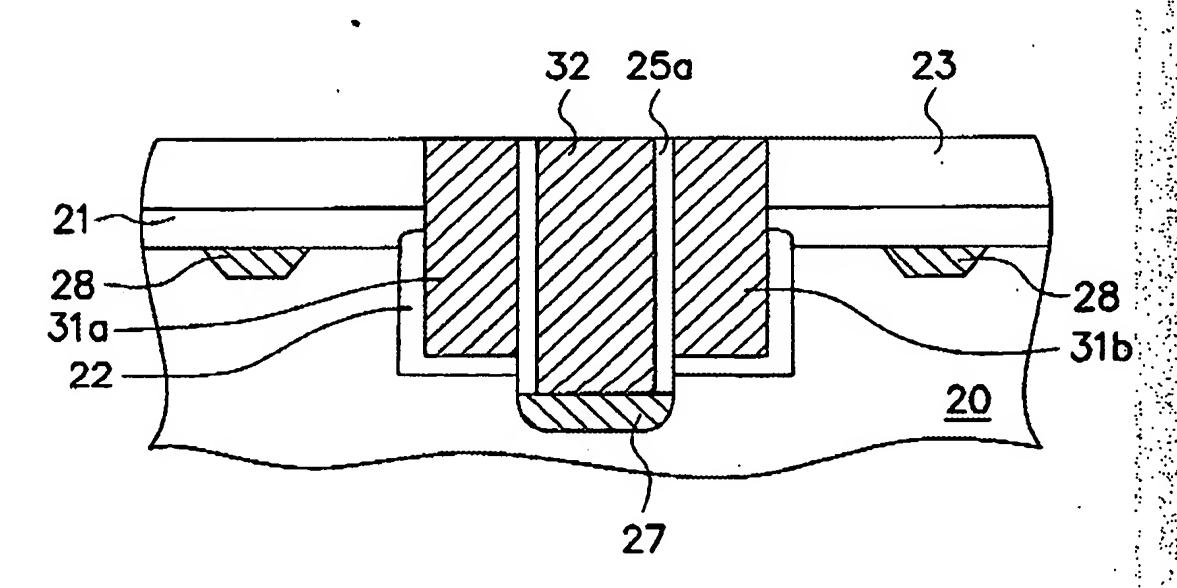


FIG. 2D(PRIOR ART)

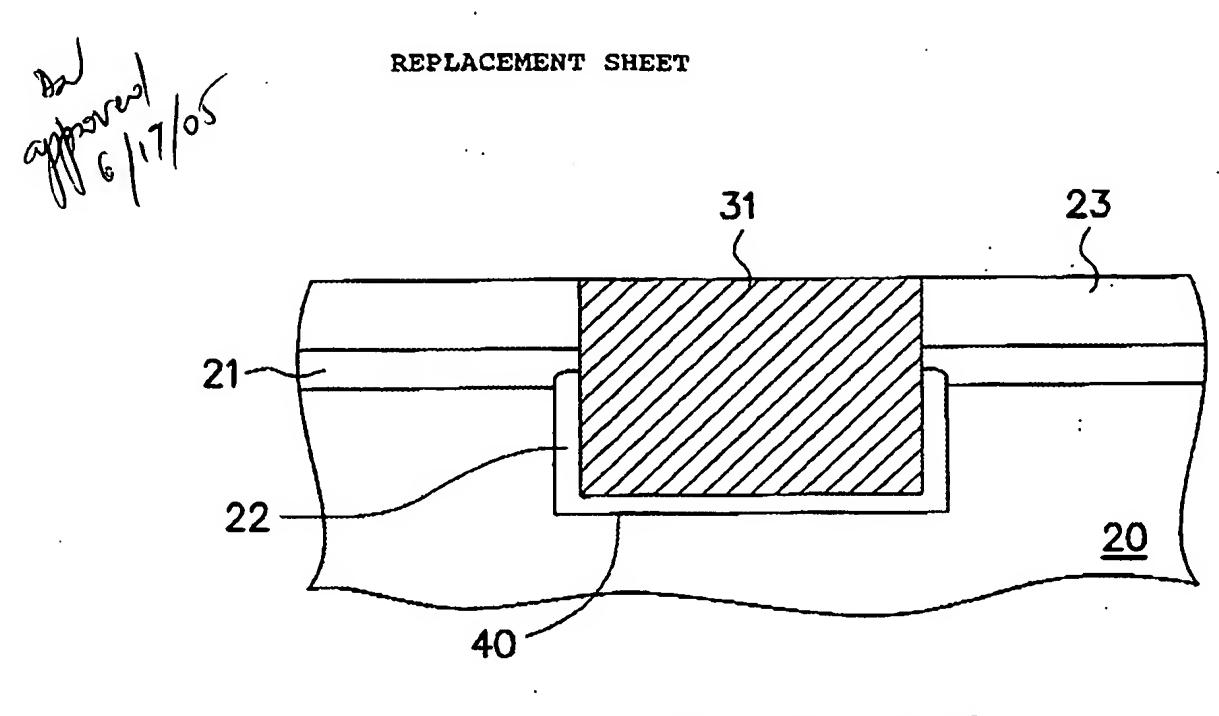


FIG. 2A(PRIOR ART)

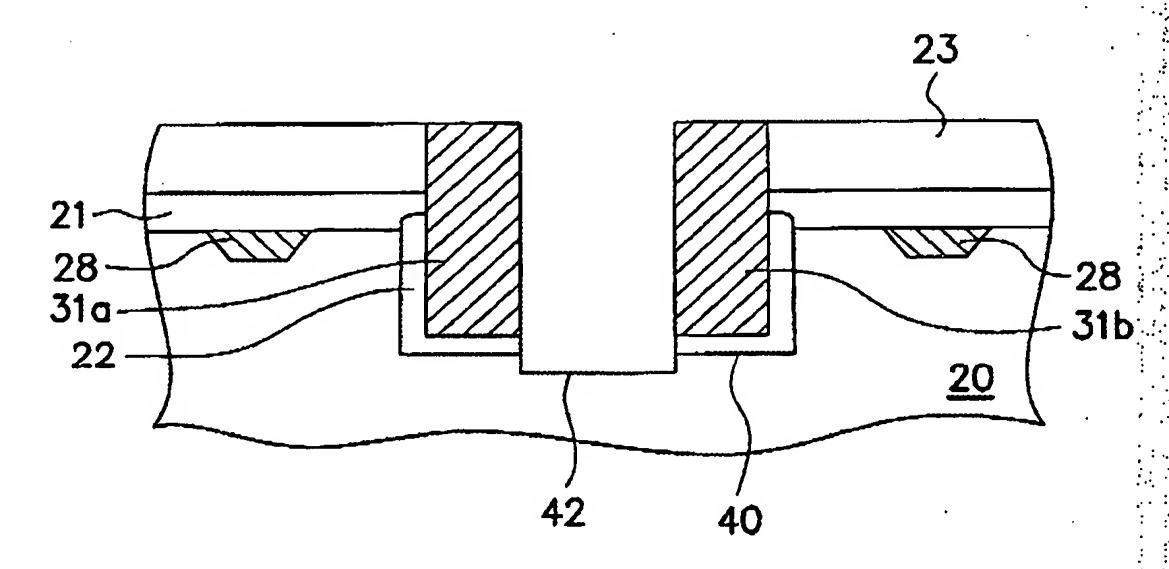


FIG. 2B(PRIOR ART)